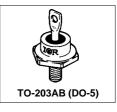
# International **ISPR** Rectifier

### SCHOTTKY RECTIFIER

### MBR7535 MBR7545

70 Amp



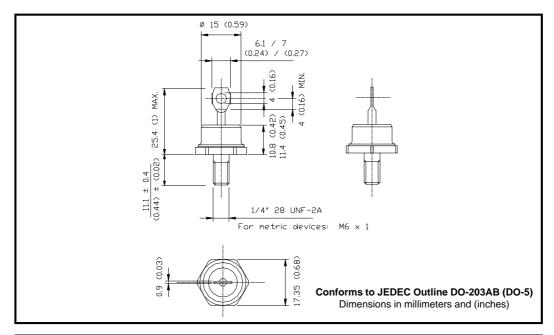
### Major Ratings and Characteristics

Characteristics	MBR75	Units
I <sub>F(AV)</sub> Rectangular waveform	70	А
V <sub>RRM</sub>	35/45	V
I <sub>FSM</sub> @ 60Hz	1000	А
V <sub>F</sub> @ 60 Apk, T <sub>J</sub> =125°C	0.60	V
TJ	- 65 to 150	°C

#### **Description/ Features**

The MBR75.. Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150° C junction temperature. Typical applications are in switching power supplies, converters, free-wheeling diodes, and reverse battery protection.

- + 150° C T<sub>J</sub> operation
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- · Hermetic packaging



www.irf.com

### MBR7535, MBR7545

Bulletin PD-2.326 rev. B 11/02

## International **tor** Rectifier

### Voltage Ratings

Part number	MBR7535	MBR7545
V <sub>R</sub> Max. DC Reverse Voltage (V)		
V <sub>RWM</sub> Max. Working Peak Reverse Voltage (V)	35	45

### Absolute Maximum Ratings

	Parameters	MBR75	Units	Conditions	
I <sub>F(AV)</sub>	Max. Average Forward Current	70	A	@ T <sub>c</sub> =90 °C, rectangular wave for	m
I <sub>FSM</sub>	Max. Peak One Cycle Non-Repetitive	9000	Α	5µs Sine or 3µs Rect. pulse	Following any rated
	SurgeCurrent	1000		Surge applied at rated load condition	In a dia any distant and
				halfwavesinglephase60Hz	applied RRM

### **Electrical Specifications**

	Parameters	MBR75	Units	C	Conditions
V <sub>FM</sub>	Max. Forward Voltage Drop(1)	0.60	V	@ 60A	T , = 125 °C
		0.90	V	@ 220A	· J ·
I <sub>RM</sub>	Max. Instantaneus Reverse Current (1)	150	mA	T <sub>J</sub> = 125 °C	Rated DC voltage
C <sub>T</sub>	Max. Junction Capacitance	4000	pF	$V_{R} = 5V_{DC}$ , (t	est signal range 100Khz to 1Mhz) 25°C
Ls	Typical Series Inductance	7.5	nH	Measured fro	om top of terminal to mounting plane
dv/dt	Max. Voltage Rate of Change (Rated $V_R$ )	10000	V/ µs		

(1) Pulse Width < 300µs, Duty Cycle <2%

### **Thermal-Mechanical Specifications**

	Parameters		MBR75	Units	Conditions
ТJ	Max. Junction Temperature R	ange	-65 to 150	°C	
T <sub>stg</sub>	Max. Storage Temperature Ra	ange	-65 to 150	°C	
R <sub>thJC</sub>	Max. Thermal Resistance Jun to Case	ction	0.83	°C/W	DCoperation
R <sub>thCS</sub>	Typical Thermal Resistance, C to Heatsink	Case	0.25	°C/W	Mounting surface, smooth and greased
wt	Approximate Weight		15(0.53)	g(oz.)	
Т	MountingTorque	Min.	23 (20)	Kg-cm	
		Max.	46 (40)	(Ibf-in)	
	CaseStyle		DO-203AB	(DO-5)	JEDEC

\* For Additional Informations and Graphs, Please See the 75HQ Series

International	MBR7535, MBR7545
<b>ISR</b> Rectifier	Bulletin PD-2.326 rev. B 11/02

Data and specifications subject to change without notice. This product has been designed for Industrial Level. Qualification Standards can be found on IR's Web site.

International **tor** Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105 TAC Fax: (310) 252-7309 Visit us at www.irf.com for sales contact information. 11/02

www.irf.com